

### FEATURES

- 1.10 mm X 0.30 mm active area
- Low slope multiplication curve
- High speed, low noise
- NIR enhanced

### DESCRIPTION

0.33 mm<sup>2</sup> High Speed, Low Noise Avalanche Photodiode with N on P construction. Hermetically packaged in a TO-5 with a clear borosilicate glass window cap.

### APPLICATIONS

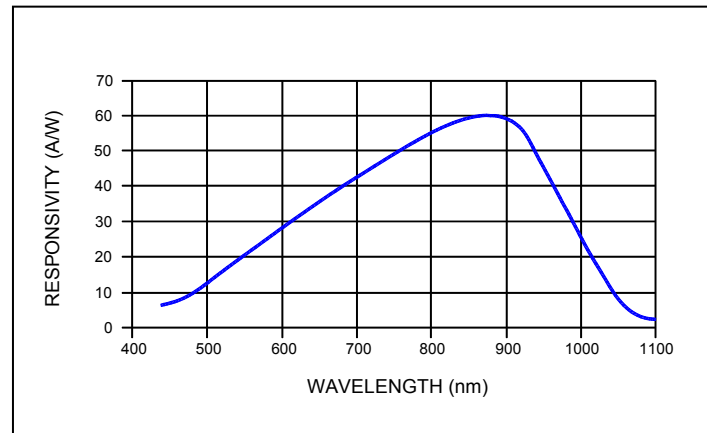
- High speed optical communications
- Laser range finder
- Medical equipment
- High speed photometry



### ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	MIN	MAX	UNITS
T <sub>STG</sub>	Storage Temp	-60	+100	°C
T <sub>OP</sub>	Operating Temp	-20	+70	°C
T <sub>SOLDERING</sub>	Soldering Temp 10 seconds		+260	°C
	Electrical Power Dissipation @ 22°C	-	100	mW
	Optical Peak Value, once for 1 second	-	200	mW
I <sub>PH</sub> (DC)	Continuous Optical Operation	-	250	µA
I <sub>PH</sub> (AC)	Pulsed Signal Input 50 µs "on" / 1 ms "off"	-	1	mA

### SPECTRAL RESPONSE at M = 100



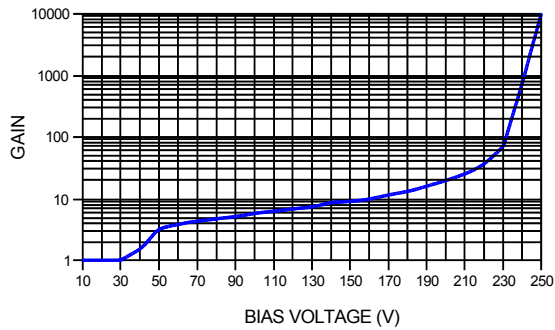
### ELECTRO-OPTICAL CHARACTERISTICS @ 22 °C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>D</sub>	Dark Current	M = 100*	---	2.0	6.0	nA
C	Capacitance	M = 100*	---	2.0	---	pF
V <sub>BR</sub>	Breakdown Voltage	I <sub>D</sub> = 2 µA	120	200	---	V
	Temperature Coefficient of V <sub>BR</sub>		---	1.55	---	V/K
	Responsivity	M = 100; = 0 V; λ = 905 nm	55	60	---	A/W
Δf <sub>3dB</sub>	Bandwidth	-3dB	---	0.35	---	GHz
t <sub>r</sub>	Rise Time	M = 100	---	1.0	---	ns
	Optimum Gain		50	60	---	
	"Excess Noise" factor	M = 100	---	2.5	---	
	"Excess Noise" index	M = 100	---	0.2	---	
	Noise Current	M = 100	---	0.75	---	pA/Hz <sup>1/2</sup>
	Max Gain		200	---	---	
NEP	Noise Equivalent Power	M = 100; λ = 905 nm	---	3.0 X 10 <sup>-14</sup>	---	W/Hz <sup>1/2</sup>

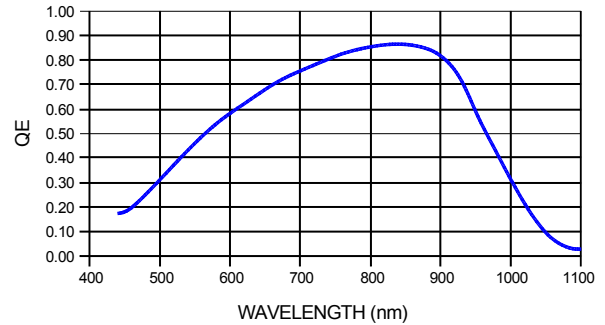
\* Measurement conditions: Setup of photo current 10 nA at M = 1 and irradiated by a 880 nm, 80 nm bandwidth LED. Increase the photo current up to 1 µA, (M = 100) by internal multiplication due to an increasing bias voltage.

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

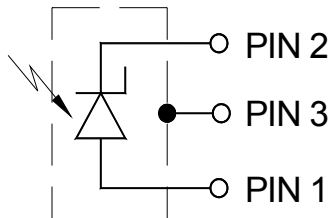
## TYPICAL GAIN vs BIAS VOLTAGE



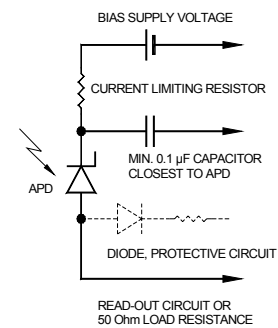
## QUANTUM EFFICIENCY for M = 100



## DEVICE SCHEMATIC



## SUGGESTED CIRCUIT SCHEMATIC



## APPLICATION NOTES

- Current should be limited by a protecting resistor or current limiting IC inside the power supply.
- Use of low noise read-out IC.
- For high gain applications ( $M > 50$ ) bias voltage should be temperature compensated.
- For low light level applications, blocking of ambient light should be used.

## HANDLING PRECAUTIONS:

- Soldering temperature - 260°C for 10 seconds max. The device must be protected against solder flux vapor.
- Minimum pin length - 2 mm
- ESD protection - Standard precautionary measures are sufficient.
- Storage - Store devices in conductive foam.
- Avoid skin contact with window.
- Clean window with Ethyl alcohol if necessary.
- Do not scratch or abrade window.

### USA:

Pacific Silicon Sensor, Inc.  
 5700 Corsa Avenue, #105  
 Westlake Village, CA 91362 USA  
 Phone (818) 706-3400  
 Fax (818) 889-7053  
 Email: [sales@pacific-sensor.com](mailto:sales@pacific-sensor.com)  
[www.pacific-sensor.com](http://www.pacific-sensor.com)

### International sales:

Silicon Sensor International AG  
 Peter-Behrens-Str. 15  
 D-12459 Berlin, Germany  
 Phone +49 (0)30-63 99 23 10  
 Fax +49 (0)30-63 99 23 33  
 Email: [sales@silicon-sensor.de](mailto:sales@silicon-sensor.de)  
[www.silicon-sensor.de](http://www.silicon-sensor.de)